# MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet

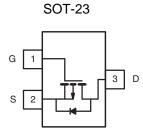












#### **Features**

- -20V,-5.5A, RDS(ON) =25 $m\Omega$ @VGS = -4.5V
- Improved dv/dt capability
- Fast switching
- Green Device Available

#### **Applications**

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

BVDSS	RDSON	ID
-12V	25mΩ	-5.5A

#### Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-12	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
1	Drain Current – Continuous (T <sub>C</sub> =25°C)	-5.5	А
lD	Drain Current – Continuous (T <sub>C</sub> =100°C)	-3.5	А
I <sub>DM</sub>	Drain Current – Pulsed¹	-21.2	А
D	Power Dissipation (Tc=25°C)	1.56	W
$P_{D}$	Power Dissipation – Derate above 25°C	0.012	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient		80	°C/W



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-12			V
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient Reference to 25°C , I <sub>D</sub> =-1mA			-0.02		V/°C
	Drain Source Leakage Current	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			-1	uA
I <sub>DSS</sub> Drain-Source Leakage Current	V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			-10	uA	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V , V <sub>DS</sub> =0V			±100	nA

#### **On Characteristics**

		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-4A		25	35	m0
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS}$ =-2.5 $V$ , $I_D$ =-3 $A$		35	50	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	\/ -\/ \ \ - 250uA	-0.3	-0.6	-1	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D$ =-250uA		2		mV/°C
gfs	Forward Transconductance	V <sub>DS</sub> =-12V , I <sub>S</sub> =-3A		8.4		S

#### **Dynamic and switching Characteristics**

•	•			
$Q_g$	Total Gate Charge <sup>2, 3</sup>		 16.1	
$Q_{gs}$	Gate-Source Charge <sup>2, 3</sup>	$V_{DS}$ =-10V , $V_{GS}$ =-4.5V , $I_{D}$ =-4A	 1.8	 nC
$Q_{gd}$	Gate-Drain Charge <sup>2, 3</sup>		 3.8	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>		 8.2	
Tr	Rise Time <sup>2, 3</sup>	$V_{DD}$ =-10V , $V_{GS}$ =-4.5V , $R_{G}$ =25 $\Omega$	 30	 nS
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>	I <sub>D</sub> =-1A	 71.1	 113
T <sub>f</sub>	Fall Time <sup>2, 3</sup>		 19.8	
C <sub>iss</sub>	Input Capacitance		 1440	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , F=1MHz	 155	 pF
C <sub>rss</sub>	Reverse Transfer Capacitance		 115	

### **Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V =V =0V Force Current			-5.5	Α
I <sub>SM</sub>	Pulsed Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-21.2	Α
$V_{SD}$	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C			-1.2	V

#### Note:

- 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width  $\leqq 300 \text{us}$  , duty cycle  $\leqq 2\%.$
- 3. Essentially independent of operating temperature.

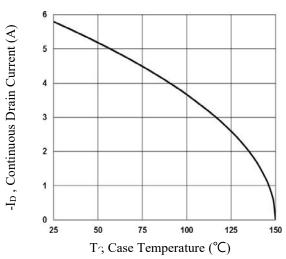


Fig.1 Continuous Drain Current vs. Tc

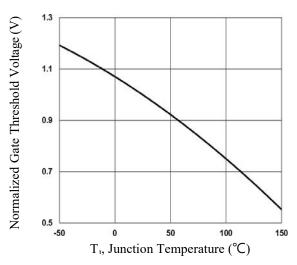


Fig.3 Normalized  $V_{th}$  vs.  $T_J$ 

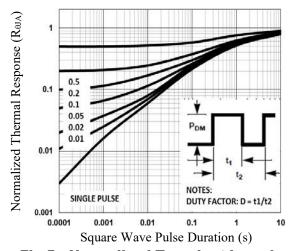
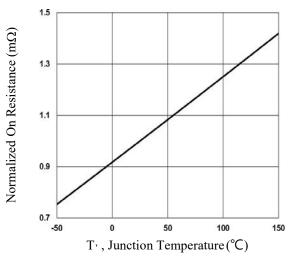


Fig.5 Normalized Transient Impedance



Normalized RDSON vs. T<sub>J</sub> Fig.2

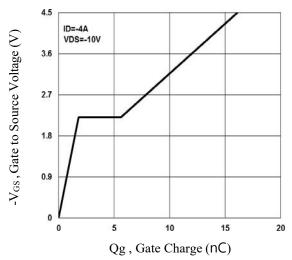


Fig.4 **Gate Charge Waveform** 

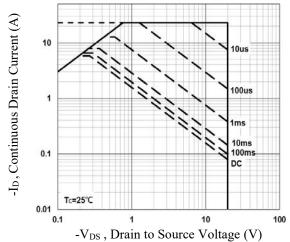
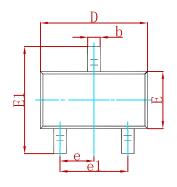


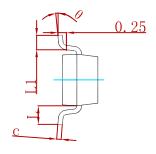
Fig.6 Maximum Safe Operation Area

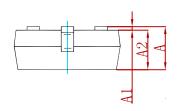


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### **PACKAGE MECHANICAL DATA**

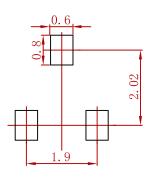






Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
Е	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.550	REF	0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

# **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

# **REEL SPECIFICATION**

P/N	PKG	QTY
SI2305CDS	SOT-23	3000



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